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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

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Charles Ahn et al.

Serial No.: 10/582,813

Art Unit: 2818

Filed: June 14, 2006

Title: Magnetoelectronic Devices Based on Colossal Magnetoresistive Thin Films

Commissioner for Patents
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INFORMATION DISCLOSURE STATEMENT

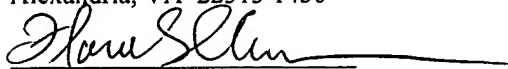
Pursuant to Sections 609 and 707.05(b) of the MPEP and 37 CFR 1.97-1.99, the attached form PTO-1449 lists documents that may be pertinent to the invention as claimed in the above-identified application.

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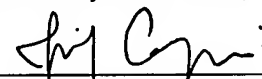
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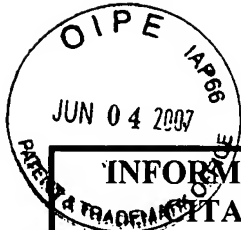
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**INFORMATION DISCLOSURE
ATTENTION FORM FOR
PATENT APPLICATION
(FORM PTO-1449)
(Substitute)**

Docket No.: 26068-27B

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Applicant: Charles Ahn et al.

Filing Date: 6/14/06

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